

P-Channel 20-V (D-S) MOSFET

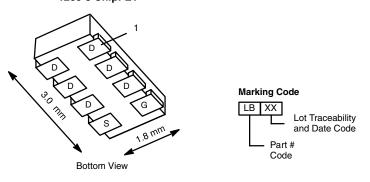
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
- 20	0.062 at V _{GS} = - 4.5 V	- 5.1		
	0.068 at V _{GS} = - 3.6 V	- 4.9		
	0.085 at V _{GS} = - 2.5 V	- 4.4		
	0.120 at V _{GS} = - 1.8 V	- 3.7		

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- ESD Protected^b 5000 V



1206-8 ChipFET®



G Φ 5.4 kΩ

Ordering Information: Si5463EDC-T1-E3 (Lead (Pb)-free)

Si5463EDC-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Drain Current /T 150 °C\d	T _A = 25 °C	- I _D	- 5.1	- 3.8		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		- 3.7	- 2.7		
Pulsed Drain Current		I _{DM}	- 15		Α	
Continuous Source Current ^a		I _S	- 1.9	- 1.0		
Marrian na Danier Disain attant	T _A = 25 °C	- P _D	2.3	1.25	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.2	0.65		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{c, d}			260			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana hardin ta Andriada	t ≤ 5 s	- R _{thJA}	45	55	°C/W
Maximum Junction-to-Ambient ^a	Steady State		84	100	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	20	25	

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. When using HBM. The MM rating is 300 V.
- c. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

Vishay Siliconix



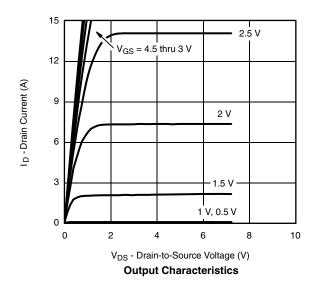
SPECIFICATIONS $T_J = 25$ °	C, unless of	otherwise noted						
Parameter	Symbol	Test Conditions Min.		Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.45			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 1.5			
Zava Cata Valtaga Drain Current		V _{DS} = - 16 V, V _{GS} = 0 V		- 1	μΑ			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 16 V, V _{GS} = 0 V, T _J = 85 °C			- 5	1		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 15			Α		
		V _{GS} = - 4.5 V, I _D = - 4.0 A		0.051	0.062			
Durin Course On Olata Basistana a	R _{DS(on)}	V _{GS} = - 3.6 V, I _D = - 3.5 A		0.056	0.068	Ω		
Drain-Source On-State Resistance ^a		V _{GS} = - 2.5 V, I _D = - 3.0 A		0.070	0.085			
		V _{GS} = - 1.8 V, I _D = - 1.5 A		0.100	0.120			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 4.0 A		10		S		
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.0 A, V _{GS} = 0 V		- 0.75	- 1.2	V		
Dynamic ^b								
Total Gate Charge	Qg			9.7	15			
Gate-Source Charge	Q_{gs}	V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 4.0 A		2.7		nC		
Gate-Drain Charge	Q_{gd}			1.4				
Turn-On Delay Time	t _{d(on)}			1.85	2.5			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		3.2	4.5			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_G = 6 Ω		1.9	2.5	μs		
Fall Time	t _f			3.2	4.5			

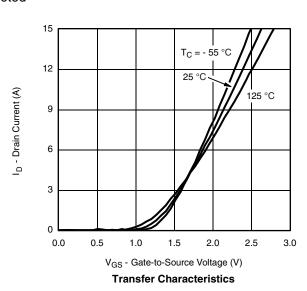
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

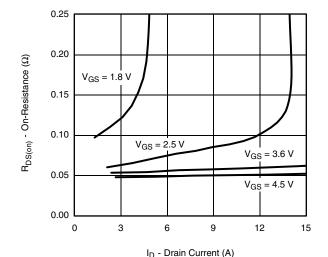
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



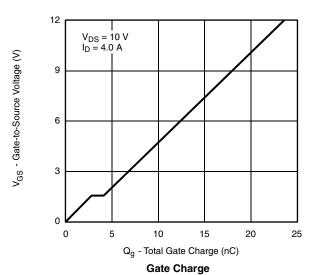


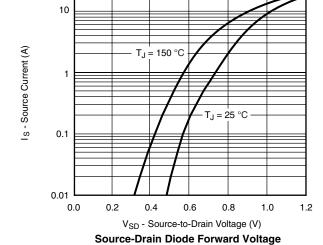


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current

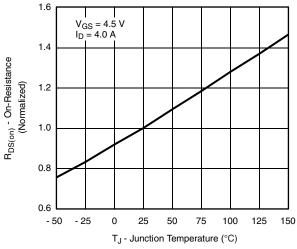




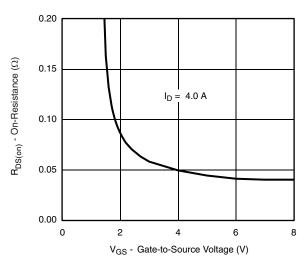
2000 C_{iss} C_{iss} 1500 C_{rss} 1000 C_{rss} 1000 C_{rss} 1000 C_{rss} 200 C_{rs} 200 C_{rss} 200 C_{rss}

V_{DS} - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature



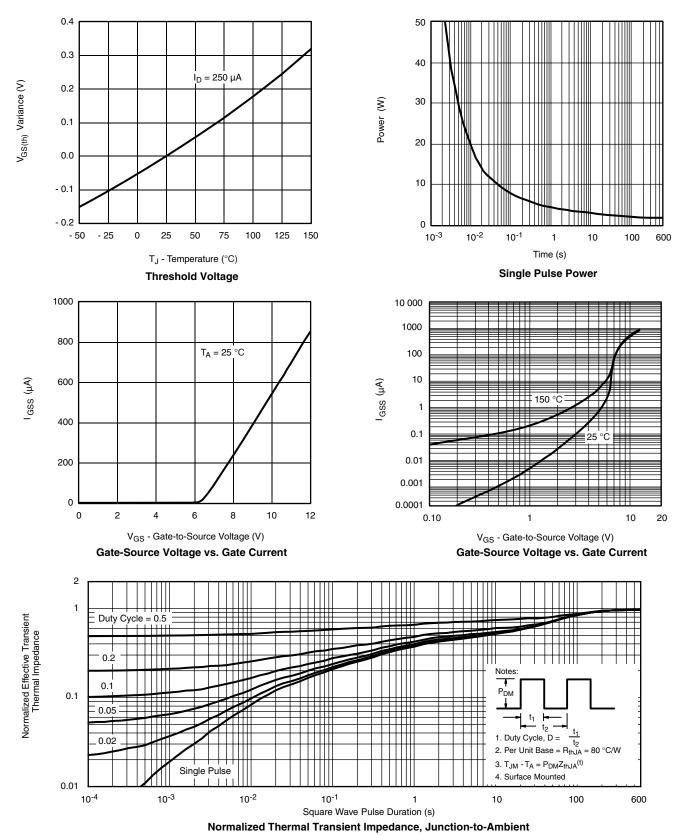
On-Resistance vs. Gate-to-Source Voltage

20

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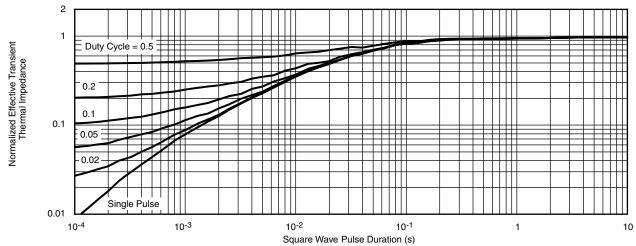
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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